## **AMENDMENTS TO THE CLAIMS:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

- 1. (currently amended) A polishing solution for metal, comprising an oxidizing agent, an oxidized-metal dissolving agent, a first protective-film forming agent, a second protective-film forming agent <u>having properties</u> different from the first protective-film forming agent, and water, <u>wherein a combination of the first protective-film forming agent and the second protective-film forming agent controls etching rate, while maintaining chemical mechanical polishing rate, of said metal.</u>
- 2. (original) The polishing solution for metal according to claim 1, wherein said first protective-film forming agent is at least one selected from a group of ammonia, amines, amino acids, imines, azoles, mercaptans and saccharides.
- 3. (original) The polishing solution for metal according to claim 2, wherein said first protective-film forming agent is at least one selected from among benzotriazole and a derivative thereof.
- 4. (original) The polishing solution for metal according to claim 1, wherein said first protective-film forming agent is a compound capable of forming a protective film by forming physical adsorption and/or chemical linkage on the metal film

surface.

- 5. (original) The polishing solution for metal according to claim 1, wherein said second protective-film forming agent is compounds having an alcoholic or phenolic hydroxyl group, esters, ethers, polysaccharides, amino acid salts, polycarboxylic acids, polycarboxylates, vinyl polymers, amides, azo compounds and molybdenum compounds.
- 6. (original) The polishing solution for metal according to claim 5, wherein said second protective-film forming agent is at least one selected from a group of polyacrylic acids, polymethacrylic acids, polyamic acids, ammonium polyacrylates, ammonium polymethacrylates, ammonium polyacrylamides.
- 7. (original) The polishing solution for metal according to claim 1, wherein said second protective-film forming agent is a compound which assists the first protective-film forming agent in forming a protective film.
- 8. (original) The polishing solution for metal according to claim 1, wherein said oxidizing agent is at least one selected from a group of hydrogen peroxide, nitric acid, potassium periodate, hypochlorous acid and ozone water.
- 9. (original) The polishing solution for metal according to claim 1, wherein said oxidized-metal dissolving agent is at least one selected from a group of an organic acid, an ammonium salt of an organic acid, and sulfuric acid.

10. (original) The polishing solution for metal according to claim 9, wherein said oxidized-metal dissolving agent is at least one selected from a group of malic acid, tartaric acid, citric acid, ammonium maliate, ammonium tartarate and ammonium citrate.

## 11.-15. (cancelled).

- 16. (currently amended) The polishing solution for metal according to claim 1, 11 or 15, which is adapted to be used to polish a metal containing at least any one of copper, a copper alloy, a copper oxide and a copper alloy oxide.
- 17. (currently amended) The polishing solution for metal according to claim 1, 41-or 15, which substantially does not contain any abrasive grains.
- 18. (original) The polishing solution for metal according to claim 1, wherein said second protective-film forming agent is a compound which enables the first protective-film forming agent to be added in a smaller quantity; the first protective-film forming agent being necessary for controlling etching rate to 10 nm/minute or lower.
- 19. (currently amended) A polishing method comprising polishing a metal film formed on the surface of a polishing object, in the polishing solution for metal according to claim 1, <del>11 or 15</del> to remove the metal film.

- 20. (original) The polishing method according to claim 19, wherein said metal film contains at least any one of copper, a copper alloy, a copper oxide and a copper alloy oxide.
- 21. (original) The polishing method according to claim 19, wherein; said polishing object has a multi-layer film having a metal layer containing at least any one of copper, a copper alloy, a cooper oxide and a copper alloy oxide; said polishing method being a method of removing at least part of the metal film from the multi-layer film.
- 22. (original) The polishing method according to claim 19, wherein said polishing solution for metal substantially does not contain any abrasive grains.
  - 23.-33. (cancelled)
- 34. (new) The polishing solution for metal according to claim 1, having a chemical mechanical polishing rate of said metal of at least 100 nm/minute and an etching rate of said metal of at most 10 nm/minute.
- 35. (new) The polishing solution for metal according to claim 34, wherein said etching rate of said metal is at most 1 nm/minute.
  - 36. (new) The polishing solution for metal according to claim 34, wherein said

chemical mechanical polishing rate of said metal is at least 250 nm/minute.

- 37. (new) The polishing solution for metal according to claim 34, wherein said metal is selected from the group consisting of copper, a copper alloy, copper oxide and a copper alloy oxide.
- 38. (new) The polishing solution for metal according to claim 5, wherein said first protective-film forming agent is at least one selected from a group of ammonia, amines, amino acids, imines, azoles, mercaptans and saccharides.
- 39. (new) The polishing solution for metal according to claim 6, wherein said first protective-film forming agent is at least one selected from among benzotriazole and a derivative thereof.
- 40. (new) The polishing solution for metal according to claim 1, wherein the first protective-film forming agent is an agent which, in a comparison polishing solution together with the oxidizing agent, the oxidized –metal dissolving agent and water, and without the second protective-film forming agent, etches the metal at an etching rate of at most 10 nm/minute, and forms a sufficiently strong protective film on the metal so as substantially not to be removed therefrom; and the second protective-film forming agent is an agent such that said combination, in said polishing solution, controls the etching rate to an etching rate of at most 10 nm/minute while permitting said chemical mechanical polishing of the metal to be performed.

- 41. (new) The polishing solution for metal according to claim 1, wherein the first protective-film forming agent is an agent which, in a comparison polishing solution together with the oxidizing agent, the oxidized —metal dissolving agent and water, and without the second protective-film forming agent, etches the metal at an etching rate of at most 10 nm/minute, and forms a sufficiently strong protective film on the metal so as substantially not to be removed therefrom by a polishing pad; and the second protective-film forming agent is an agent such that said combination, in said polishing solution, controls the etching rate to an etching rate of at most 10 nm/minute while permitting said chemical mechanical polishing of the metal to be performed using a polishing pad.
  - 42. (new) A polishing solution for metal, comprising:

a first protective-film forming agent which is a compound capable of forming a protective film by physically adsorbing the first protective-film forming agent on the metal film surface and/or chemically linking the first protective film forming agent with the metal film surface; and

a second protective-film forming agent which is a compound which assists the first protective-film forming agent in forming a protective film,

having a chemical mechanical polishing rate of the metal of at least 100 nm/minute and an etching rate of the metal of at most 10 nm/minute.

43. (new) The solution according to claim 42, consisting essentially of said first protective-film forming agent and said second protective-film forming agent.

- 44. (new) The polishing solution for metal according to claim 42, wherein said etching rate is 1 nm/minute or lower.
- 45. (new) The polishing solution for metal according to claim 42, wherein said chemical mechanical polishing rate is 250 nm/minute or higher.
- 46. (new) The polishing solution for metal according to claim 42, wherein said first protective-film forming agent is at least one selected from a group of ammonia, amines, amino acids, imines, azoles, mercaptans and saccharides.
- 47. (new) The polishing solution for metal according to claim 42, wherein said first protective-film forming agent is at least one selected from among benzotriazole and a derivative thereof.
- 48. (new) The polishing solution for metal according to claim 42, wherein said second protective-film forming agent is compounds having an alcoholic or phenolichydroxyl group, esters, ethers, polysaccharides, amino acid salts, polycarboxylic acids, polycarboxylates, vinyl polymers, amides, azo compounds and molybdenum compounds.
- 49. (new) The polishing solution for metal according to claim 42, wherein said second protective-film forming agent is at least one selected from a group of

polyacrylic acids, polymethacrylic acids, polyamic acids, ammonium polyacrylates, ammonium polymethacrylates, ammonium polyamides and polyacrylamides.

- 50. (new) The polishing solution for metal according to claim 42, wherein said metal contains at least one selected from the group consisting of copper, a copper alloy, a copper oxide and a copper alloy oxide.
- 51. (new) The polishing solution for metal according to claim 42, which substantially does not contain any abrasive grains.